EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	599764	(wafer\$1 or semicondudor\$I or chip\$I or subtrat\$1)	US PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 11:24
L2	5	L1 and (automatic adj defect adj classification or ADC) and knowledge adj based adj database	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 11:25
L5	0	L1 and(assign\$3 or test\$3 or evaluat\$3 or accept\$3)same select\$3 adj number same(defect or flaw or fault)same(plurality or plural\$1 or location or first adj wafer or wafer\$1)same (capaturing or obtaining or generating or pictures or thumbnails adj image\$1 or display\$3) same(intensity or contrast or brightness or focus or out adj focus or illumination or source or light or optimal adj illuminat\$3)	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 11:41
L6	3	L2 and(@ad<"20030712" or @rlad<"20030712" or @prad<"20030712" or @prad<"20030712")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 11:43
L7	0	L2 and @ad< "20030712"	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 11:43
L8	0	L2 and(assign\$3 or test\$3 or evaluat\$3 or accept\$3)same select\$3 adj number same(defect or flaw or fault)same(plurality or plural\$1 or location or first adj wafer or wafer\$1)same (capaturing or obtaining or generating or pictures or thumbnails adj image\$1 or display\$3) same(intensity or contrast or brightness or focus or out adj focus or illumination or source or light or optimal adj illuminat\$3)and threshold same descriptors	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 11:46
L9	11250	L2 and(assign\$3 or test\$3 or evaluat\$3 or accept\$3) and select\$3 adj number and(defect or flaw or fault) and(plurality or plural\$1 or location or first adj wafer or wafer\$1) and (capaturing or obtaining or generating or pictures or thumbnails adj image\$1 or display\$3) and0(intensity or contrast or brightness or focus or out adj focus or illumination or source or light or optimal adj illuminat\$3) and threshold\$3 and descriptors	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	:OR	ON	2009/07/02 11:47

L10	712	L9 and(wafer\$1 or semicondudor\$l or chip\$l or subtrat\$1)	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 11:47
L11	1	L10 and (automatic adj defect adj classification or ADC) and knowledge adj based adj database	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 11:48
L14	47	accept\$3)and select\$3 adj number and(defect or flaw or fault)and(plurality or plural\$1 or	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 11:52
L15	0	L14 and (automatic adj defect adj classification or ADC) and knowledge adj based adj database	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 11:53
L16	45	L14 and(@ad<"20030712" or @rlad<"20030712" or @prad<"20030712" or @prad<"20030712" or @ptad<"20030712")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 11:53
L17	4	L14 and @ad< "20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 11:53
L18	7	or flaw or fault)same(plurality or plural\$1 or location or first adj wafer or wafer\$1)same	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 11:57
L19	0	L18 and(@ad<"20030712" or @rlad<"20030712" or @prad<"20030712" or @prad<"20030712" or	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 11:57

L21	0		US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 12:02
S1	571947	(wafer\$1 or semicondudor\$I or chip\$I or subtrat\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:27
S2	1	S1 and automatic and defect adj classification and teaching and knowledge adj based adj database	US PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:29
S3	1	automatic and defect adj classification and teaching and knowledge adj based adj database	US PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:30
S4	1	S1 and defect adj classification and teaching and knowledge adj based adj database	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:30
S5	1	defect adj classification and teaching and knowledge adj based adj database	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:30
S6	2	defect adj classification and knowledge adj based adj database	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:31
S7	82	defect and classification and knowledge adj database	US PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:31

S 8	19	S7 and (wafer\$1 or semicondudor\$I or chip\$I or subtrat\$1)	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:31
S9	17	S3 and(@ad<"20030712" or @rlad<"20030712" or @prad<"20030712" or @prad<"20030712")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:36
S10	12	\$3 and @ad< "20030712"	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:36
S11	24	((DIRK) near2 (SOENKSEN)).INV.	US-PGPUB; USPAT	OR	ON	2008/12/05 11:36
S12	11	((RALF) near2 (FRIEDRICH)).INV.	US-PGPUB; USPAT	OR	ON	2008/12/05 11:37
S13	1	((ANDREAS) near2 (DRAEGER)).INV.	US-PGPUB; USPAT	OR	ON	2008/12/05 11:37
S14	2	((DETLEF) near2 (SCHUPP)).INV.	US-PGPUB; USPAT	OR	ON	2008/12/05 11:37
S16	2	((THIN) near2 ("VAN LUU")).INV.	US-PGPUB; USPAT	OR	ON	2008/12/05 11:39
S17	3	((WOLFGANG) near2 (LANGER)).INV.	US-PGPUB; USPAT	OR	ON	2008/12/05 11:39
S18	0	S11 and defect and classification and knowledge adj database	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:40
S19	0	S11 and defect and classification and knowledge adj database	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:40
S20	0	S11 and defect and classification and knowledge adj database	US PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:41

S21	0	S12 and defect and classification and knowledge adj database	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:41
S22	0	S13 and defect and classification and knowledge adj database	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:43
S23	3	S10 and descriptor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:46
S24	638382	S23 and select\$3 and review and data file	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:47
S25	0	\$23 and select\$3 and review and data adj file	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:47
S26	18	S7 and select\$3 and review and data adj file	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:48
S27	0	S26 and parameters and learning adj node	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:49
S28	0	S26 and parameters and learning adj mode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:49
S29	17	S26 and parameters	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:49

S30	2	S1 and S7 and S24 and S29	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:56
S31	2	S30 and @ad<"20030712"	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:56
S32	18	S7 and S26	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:57
S33	16	S32 and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 11:58
S34	20	S1 and automatic and defect adj recognition	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:00
S 35	638382	S34 and select\$3 and review and data file	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:01
S36	4	S34 and descriptor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:33
S37	1	S34 and learning adj mode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:34
S38	0	S37 and @ad< "20030712"	US PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:34

S39	16	S34 and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:35
S40	0	339 and learning adj mode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:35
S41	2	S39 and learning	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:35
S42	16	\$26 and @ad< "20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:39
S43	0	S42 and learning adj mode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:40
S44	0	S42 and learning near mode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:40
S45	0	S42 and learning near3 mode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:40
S46	11	S42 and descriptor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:40
S47	598	S1 and select\$3 and review and data adj file	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:44

S48	340	S47 and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:44
S49	1	S48 and input and user and learning adj mode	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:45
S50	1	S48 and learning adj mode	US PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:46
S51	4	S48 and alignment adj procedure	US PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 12:46
S52	0	\$\mathrm{38}\$ and automatic adj defect and recognition and(detect\$3 or determining)same (defect or flaw or fault)same(assign\$3 or test\$3 or evaluat\$3)same descriptor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 13:02
S53	0	\$48 and automatic adj defect and recognition and(detect\$3 or determining)same (defect or flaw or fault)same(assign\$3 or test\$3 or evaluat\$3)same descriptor	US-PGPUB; USPAT; EPO; UPO; DERWENT; BM_TDB	OR	ON	2008/12/05 13:02
S54	1	automatic adj defect and recognition and(detect\$3 or determining)same (defect or flaw or fault)same(assign\$3 or test\$3 or evaluat\$3)same descriptor	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 13:02
S55	11	automatic adj defect and recognition and(detect\$3 or determining)and(defect or flaw or fault)and(assign\$3 or test\$3 or evaluat\$3)and descriptor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 13:03
S56	5	\$55 and @ad< "20030712"	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 13:03

S57	1	S56 and learning adj mode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 13:03
S58	0	S57 and edit adj recipe	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 13:05
S59	0	S57 and edit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 13:05
S60	0	S57 and memory adj circuits	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 13:07
S61	1	S57 and circuits	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 13:07
S62	0	S61 and logic adj circuits	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 13:08
S63	0	S61 and blank adj wafer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 13:08
S64	1	S56 and learning adj mode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/05 14:02
S65	571947	(wafer\$1 or semicondudor\$I or chip\$I or subtrat\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:12

S66	2	S65 and select\$3 and review adj data adj file	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:13
S67	2	S65 and review adj data adj file	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:13
S68	638	S65 and review and data adj file	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:14
S69	134	S65 and review same data adj file	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:14
S70	0	S69 and defect and classification and knowledge adj database	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:15
S71	0	S69 and classification and knowledge adj database	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:15
S72	1	S69 and classification and knowledge near3 database	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:15
S73	11	S68 and classification and knowledge near3 database	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:15
S74	5	\$73 and @ad< "20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:16

S75	5	S74 and review and data adj file	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:16
S76	1	S75 and (user or operator or human)and page and learning adj mode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:17
S77	1	S75 and (user or operator or human)and learning adj mode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:17
S78	9	S68 and(detect\$3 or determining) and (defect or fault or flaw)and classification and knowledge near3 database	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:19
S79	13	learning and(knowledge-based or knowledge adj based) and database and automatic and defect adj classification	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:21
S80	10	S79 and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:21
S81	0	Section 2015 (Section 2015) Se	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:21
S82	1	S80 and data adj file	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:22
S83	8	980 and(wafer\$1 or semicondudor\$1 or chip\$1 or subtrat\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:24

S84	8	S83 and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	OR	ON	2008/12/06 11:24
\$85	6	384 and descriptor	US PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:43
S86	5	S84 and descriptor adj (defect or fault or flaw)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/06 11:46
S87	573639	(wafer\$1 or semicondudor\$l or chip\$l or subtrat\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:04
S88	19	S87 and defect and classification and knowledge adj database	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:05
S89	640949	S88 and select\$3 and review and data file	US PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:05
S90	2	S88 and select\$3 and review and data adj file	US PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:05
S91	8	987 and display adj thumbnails	US PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:07
S92	2	991 and @ad<"20030712"	US PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:07

S93	0	\$92 and descriptor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:15
S94	8	991 and parameters	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:27
S95	1	\$94 and automatic adj defect and recognition and(detect\$3 or determining)and(defect or flaw or fault)and(assign\$3 or test\$3 or evaluat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:29
S96	2	S92 and display adj thumbnails	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:30
S97	2	S96 and parameters	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:30
S98	0	S97 and circuits	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:31
S99	0	S97 and defect and (classification or classifier or classify)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:32
S100	0	S97 and(classification or classifier or classify or grouping)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:33
S101	0	S97 and intensity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:33

S102	2	997 and (intensity or contrast or brightness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:34
S103	2	S102 and(illumination or source or light)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:34
S104	2	S103 and(blank adj wafer\$1 or wafer\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:36
S105	2	S104 and(polymer or layer or oxide adj layer or contact or metal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:38
S106	0	S105 and lens	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:39
S107	0	S105 and focus	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:39
S108	0	S105 and magnificat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:40
S109	2	S105 and @ad< "20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:40
S110	2	S109 and select\$3 adj recipe	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/17 19:41

S111	2	"6973209".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT;	OR	ON	2008/12/19 15:40
S112	0	S111 and alignment	US-PGPUB; US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:40
S113	1	S111 and align\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:40
S114	0	S111 and align\$3 same light	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:41
S115	1	S111 and align\$3 and(light or source or illuminat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:41
S116	1	S115 and adjusting	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:42
S117	0	S116 and optimal adj intensity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:42
S118	1	S116 and optimal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:42
S119	0	S118 and intensity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:42

S120	1	S118 and parameters	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:43
S121	1	S120 and algorithm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:46
S122	1	S121 and automatic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:47
S123	0	S122 and intensity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:47
S124	1	S122 and (intensity or contrast or brightness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:47
S125	0	S124 and text adj image\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:48
S126	0	S124 and text	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:48
S127	1	S124 and recipe	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:49
S128	0	S127 and review	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:49

S129	1	S127 and dictionary	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:49
S130	1	S129 and registered	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:50
S131	1	S130 and drag	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 15:51
S132	82	defect and classification and knowledge adj database	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 16:09
S133	18	S132 and select\$3 and review and data adj file	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 16:09
S134	16	S133 and @ad< "20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 16:09
S135	0	S132 and select\$3 same review adj data	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 16:13
S136	5	S132 and review adj data	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 16:13
S137	3	S136 and @ad< "20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 16:14

S138	1	S137 and descriptors	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 16:19
S139	0	S137 and defect adj descriptors	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/19 16:20
S140	82	defect and classification and knowledge adj database	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 11:44
S141	5	S140 and review adj data	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 11:44
S142	3	S141 and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 11:44
S143	2	S142 and(wafer\$1 or semicondudor\$I or chip\$I or subtrat\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 11:45
S144	3	"6408219".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 11:46
S145	1	S144 and review adj data	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 11:47
S146	1	S144 and select\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 11:48

S147	732	select\$3 same review adj data	US-PGPUB; USPAT; EPO; UPO; DERWENT;	OR	ON	2008/12/30 11:50
S148	62	\$147 and(wafer\$1 or semicondudor\$l or chip\$l or subtrat\$1)	US-PGPUB; USPAT; EPO; UPO; DERWENT; BM_TDB	OR	ON	2008/12/30 11:50
S149	0	S148 and defect and classification and knowledge adj database	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 11:50
S150	0	S148 and classification and knowledge adj database	US-PGPUB; USPAT; EPO; JPO; DERWENT; BM_TDB	OR	ON	2008/12/30 11:50
S151	14	S148 and @ad<"20030712"	US-PGPUB; USPAT; EPO; UPO; DERWENT; BM_TDB	OR	ON	2008/12/30 11:51
S152	0	S151 and display adj thumbnails	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 11:51
S153	0	S151 and display and thumbnails	US-PGPUB; USPAT; EPO; UPO; DERWENT; BM_TDB	OR	ON	2008/12/30 11:52
S154	0	S151 and thumbnails	US-PGPUB; USPAT; EPO; UPO; DERWENT; BM_TDB	OR	ON	2008/12/30 11:52
S155	0	S151 and automatic and defect adj recognition	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:12

S156	0	S151 and select\$3 adj recipe	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:13
S157	1	S151 and align\$3 and(light or source or illuminat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:13
S158	0	S157 and(user or operator or human)and page and learning adj mode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:16
S159	0	S157 and descriptors	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:16
S160	0	S157 and parameters	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:36
S161	11	automatic adj defect and recognition and(detect\$3 or determining)and(defect or flaw or fault)and(assign\$3 or test\$3 or evaluat\$3)and descriptor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 15:58
S162	5	S161 and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 15:58
S163	1	S162 and learning adj mode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 15:58
S164	0	S163 and memory adj circuits	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 15:58

S165	575216	(wafer\$1 or semicondudor\$l or chip\$l or subtrat\$1)	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 15:58
S166	10	\$165 and automatic adj defect and recognition and(detect\$3 or determining)and(defect or flaw or fault)and(assign\$3 or test\$3 or evaluat\$3)and descriptor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 15:59
S167	643423	S166 and select\$3 and review and data file	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 15:59
S168	1	S166 and select\$3 and review and data adj file	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:00
S169	0	S168 and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; BM_TDB	OR	ON	2008/12/31 16:00
S170	1	S166 and memory adj circuits	US-PGPUB; USPAT; EPO; JPO; DERWENT; BM_TDB	OR	ON	2008/12/31 16:00
S171	0	S170 and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; BM_TDB	OR	ON	2008/12/31 16:01
S172	4	S166 and @ad< "20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; BM_TDB	OR	ON	2008/12/31 16:01
S173	0	S172 and memory adj circuits	US-PGPUB; USPAT; EPO; JPO; DERWENT; BM_TDB	OR	ON	2008/12/31 16:01

S174	7745	S165 and memory adj circuits	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:01
S175	2341	S174 and parameters	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:01
S176	775	S175 and logic adj circuits	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:02
S177	9	S176 and blank adj wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:02
S178	8	S177 and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:03
S179	0	S178 and resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:03
S180	0	S178 and photo adj resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:03
S181	0	S178 and polymer adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:04
S182	51765	polymer adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:04

S183	33269	S182 and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:04
S184	2388	S183 and oxide adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:05
S185	1703	S184 and contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:05
S186	16332	S183 and contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:05
S187	10	S186 and metal adj later	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:06
S188	1	S187 and parameters	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:06
S189	1	S188 and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:06
S190	1	S189 and(intensity or contrast or brightness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:07
S191	0	S190 and align\$3 and(light or source or illuminat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:07

S192	1	S190 and(light or source or illuminat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:07
S193	0	S192 and magnificat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:08
S194	0	S192 and lens	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:08
S195	0	S192 and histogram	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:08
S196	0	S195 and focus\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/31 16:12
S197	51832	polymer adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:04
S198	33269	S197 and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:04
S199	16332	S198 and contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:04
S200	10	S199 and metal adj later	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:04

S201	1	\$200 and parameters	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:04
S202	1	S201 and @ad<"20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:04
S203	1	\$202 and(intensity or contrast or brightness)	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:04
S204	1	S203 and(light or source or illuminat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:04
S205	0	S204 and metal adj layer	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:05
S206	1	S204 and metal	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:06
S207	0	206 and bright adj field	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:07
S208	0	Stand bright	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:07
S209	1	\$206 and (UV or DUV)	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:08

S210	0	S209 and lens	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:08
S211	0	© 209 and intensity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:09
S212	1	\$209 and contrast	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:10
S213	0	S212 and histogram	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:10
S214	795256	select\$3 and review and data file	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:12
S215	2665	S214 and polymer adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:13
S216	12	S≥15 and bright adj field	US PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:13
S217	9	S216 and (UV or DUV)	US PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:13
S218	3	S≥17 and @ad< "20030712"	US PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:13

S219	3	S218 and intensity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:13
S220	0	S219 and histogram	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:14
5221	0	S219 and metal adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:14
5222	0	№ 219 and lens	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:14
223	4	S216 and lens	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:15
224	0	\$223 and @ad<"20030712"	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:15
\$225	0	\$223 and @ad<"20030712"	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2009/01/02 14:15
S226	5025	382/149,145,224,159,100,141,155,181.CQLS.	USPAT	OR	ON	2009/06/29 11:58
3227	4478	715/774,835,837,764,841,210,839,762,809,804,973,250,866,708.CCLS.	USPAT	OR	ON	2009/06/29 12:01
228	1453	719/310,315.CCLS.	USPAT	OR	ON	2009/06/29 12:01
\$229	355	714/E11.21.COLS.	USPAT	OR	ON	2009/06/29 12:02

S230	1846	356/237.1,237.2.00LS.	USPAT	OR	ON	2009/06/29 12:03
S231	834	702/35,1,33.CCLS.	USPAT	OR	ON	2009/06/29 12:04
S232	599018	(wafer\$1 or semicondudor\$I or chip\$I or subtrat\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 12:29
S233	125	S232 and user adj select\$3 and review and data adj file	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 12:32
S234	3	S233 and input adj user and page and learning adj mode and parameters	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 12:34
S235	4	S233 and input and user and page and learning adj mode and parameters	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 12:37
S236	4	S233 and learning adj mode and parameters	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 12:55
S237	1	\$233 and automatic adj defect and recognition and(detect\$3 or determining)and(defect or flaw or fault)and(assign\$3 or test\$3 or evaluat\$3)and descriptor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 12:58
S238	11	automatic adj defect and recognition and(detect\$3 or determining)and(defect or flaw or fault)and(assign\$3 or test\$3 or evaluat\$3)and descriptor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 12:59
S239	10	\$238 and(wafer\$1 or semicondudor\$l or chip\$l or subtrat\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 12:59

S240	1	\$239 and user adj select\$3 and review and data adj file	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 13:00
5241	1	\$239 and user adj select\$3 and review adj data	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 13:00
∑242	3	automatic adj defect and recognition and(detect\$3 or determining)and(defect or flaw or fault)and(assign\$3 or test\$3 or evaluat\$3 or accept\$3)and select\$3 adj(wafer\$1 or semicondudor\$l or chip\$l or substrat\$1)and(capturing or pictures or ccd or camera)and (illumination or source or light or optimal adj intensity or light adj intensity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 13:12
243	3	automatic adj defect and recognition and(detect\$3 or determining)and(defect or flaw or fault)and(assign\$3 or test\$3 or evaluat\$3 or accept\$3)and select\$3 adj(wafer\$1 or semicondudor\$l or chip\$l or substrat\$1)and(capturing or pictures or ccd or camera)and align\$4 and(illumination or source or light or optimal adj intensity or light adj intensity or brightness or contrast)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 13:16
244	0	\$243 and(@ad<"20030712" or @rlad<"20030712" or @prad<"20030712" or @prad<"20030712")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 13:17
246	781	\$226 and(wafer\$1 or semicondudor\$l or chip\$l or subtrat\$1)	USPAT	OR	ON	2009/06/29 13:19
247	3	\$246 and user adj select\$3 and review and data adj file	USPAT	OR	ON	2009/06/29 13:19
248	27	\$246 and user adj select\$3 and review and(storage or stored or memory or data adj file)	USPAT	OR	ON	2009/06/29 13:20
249	0	\$248 and input and user and page and learning adj mode and parameters	USPAT	OR	ON	2009/06/29 13:21
251	0	\$248 and automatic adj defect and recognition and(detect\$3 or determining)and(defect or flaw or fault)and(assign\$3 or test\$3 or evaluat\$3 or accept\$3)and select\$3 adj(wafer\$1 or semicondudor\$l or chip\$l or substrat\$1)and(capturing or pictures or ccd or camera)and align\$4 and(illumination or source or light or optimal adj intensity or light adj intensity or brightness or contrast)	USPAT	OR	ON	2009/06/29 13:23
252	0	\$248 and automatic adj defect and recognition and(detect\$3 or determining)and(defect or flaw or fault)and(assign\$3 or test\$3 or evaluat\$3 or accept\$3)and select\$3 adj(wafer\$1 or semicondudor\$l or chip\$l or substrat\$1)and(capturing or pictures or ccd or camera)and (illumination or source or light or optimal adj intensity or light adj intensity or brightness or contrast)	USPAT	OR	ON	2009/06/29 13:24

S253	2	\$248 and automatic adj defect and recognition and(detect\$3 or determining)and(defect or flaw or fault)and(assign\$3 or test\$3 or evaluat\$3 or accept\$3)	USPAT	OR	ON	2009/06/29 13:25
S254	2	\$253 and(@ad<"20030712" or @rlad<"20030712" or @prad<"20030712" or @prad<"20030712" or @ptad<"20030712")	USPAT	OR	ON	2009/06/29 13:28
S255	0	\$253 and select\$3 adj(wafer\$1 or semicondudor\$l or chip\$l or substrat\$1)and(capturing or pictures or ccd or camera)and align\$4 and(illumination or source or light or optimal adj intensity or light adj intensity or brightness or contrast)	USPAT	OR	ON	2009/06/29 13:32
S256	0	\$253 and select\$3 adj(wafer\$1 or semicondudor\$l or chip\$l or substrat\$1)and(capturing or pictures or ccd or camera)and(illumination or source or light or optimal adj intensity or light adj intensity or brightness or contrast)	USPAT	OR	ON	2009/06/29 13:43
S257	0	\$253 and select\$3 adj(wafer\$1 or semicondudor\$1 or chip\$1 or substrat\$1) and(capturing or pictures or ccd or camera) and (illumination or source or light or optimal adj intensity or light adj intensity or brightness or contrast) and (detect\$3 or determining) and (defect or flaw or fault)	USPAT	OR	ON	2009/06/29 13:46
S258	18	\$227 and(wafer\$1 or semicondudor\$l or chip\$l or subtrat\$1)	USPAT	OR	ON	2009/06/29 13:48
S259	4	\$258 and user adj select\$3 and review and(storage or stored or memory or data adj file)	USPAT	OR	ON	2009/06/29 13:48
S260	0	\$259 and automatic adj defect and recognition and(detect\$3 or determining)and(defect or flaw or fault)and(assign\$3 or test\$3 or evaluat\$3 or accept\$3)	USPAT	OR	ON	2009/06/29 13:48
S261	0	\$\sim \sim \sim \sim \sim \sim \sim \sim	USPAT	OR	ON	2009/06/29 13:52
S262	2	\$228 and(wafer\$1 or semicondudor\$l or chip\$l or subtrat\$1)	USPAT	OR	ON	2009/06/29 13:53
S263	0	\$262 and automatic adj defect and recognition and(detect\$3 or determining)and(defect or flaw or fault)and(assign\$3 or test\$3 or evaluat\$3 or accept\$3)	USPAT	OR	ON	2009/06/29 13:55
S264	0	\$262 and user adj select\$3 and review and(storage or stored or memory or data adj file)	USPAT	OR	ON	2009/06/29 13:56
S265	0	\$262 and select\$3 adj(wafer\$1 or semicondudor\$1 or chip\$1 or substrat\$1)and(capturing or pictures or ccd or camera)and align\$4 and(illumination or source or light or optimal adj intensity or light adj intensity or brightness or contrast)	USPAT	OR	ON	2009/06/29 13:56
S266	2	\$228 and(wafer\$1 or semicondudor\$l or chip\$l or subtrat\$1)	USPAT	OR	ON	2009/06/29 13:59
S267	1	S229 and(wafer\$1 or semicondudor\$l or chip\$l or subtrat\$1)	USPAT	OR	ON	2009/06/29 13:59
S268	0	\$267 and automatic adj defect and recognition and(detect\$3 or determining)and(defect or flaw or fault)and(assign\$3 or test\$3 or evaluat\$3 or accept\$3)	USPAT	OR	ON	2009/06/29 13:59
S269	0	\$267 and user adj select\$3 and review and(storage or stored or memory or data adj file)	USPAT	OR	ON	2009/06/29 13:59

S270	0	\$267 and select\$3 adj(wafer\$1 or semicondudor\$l or chip\$l or substrat\$1)and(capturing or pictures or ccd or camera)and align\$4 and(illumination or source or light or optimal adjuntensity or light adj intensity or brightness or contrast)	USPAT	OR	ON	2009/06/29 14:00
S271	733	\$230 and(wafer\$1 or semicondudor\$l or chip\$l or subtrat\$1)	USPAT	OR	ON	2009/06/29 14:01
S272	5	\$271 and automatic adj defect and recognition and(detect\$3 or determining)and(defect or fault)and(assign\$3 or test\$3 or evaluat\$3 or accept\$3)	USPAT	OR	ON	2009/06/29 14:01
S273	0	\$272 and user adj select\$3 and review and(storage or stored or memory or data adj file)	USPAT	OR	ON	2009/06/29 14:01
S274	0	\$272 and select\$3 adj(wafer\$1 or semicondudor\$l or chip\$l or substrat\$1)and(capturing or pictures or ccd or camera)and align\$4 and(illumination or source or light or optimal adjintensity or light adj intensity or brightness or contrast)	USPAT	OR	ON	2009/06/29 14:01
S275	5	\$272 and(@ad<"20030712" or @rlad<"20030712" or @prad<"20030712" or @prad<"20030712" or @prad<"20030712" or	USPAT	OR	ON	2009/06/29 14:02
S276	0	\$272 and user adj select\$3 and review and(storage or stored or memory or data adj file)	USPAT	OR	ON	2009/06/29 14:03
S277	599018	(wafer\$1 or semicondudor\$I or chip\$I or subtrat\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 14:04
S278	83	defect and classification and knowledge adj database	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 14:04
S279	19	S278 and (wafer\$1 or semicondudor\$l or chip\$l or subtrat\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 14:04
S280	12	S279 and @ad< "20030712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 14:04
S281	3	S280 and descriptor	US-PGPUB; USPAT; EPO; UPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 14:04

S282	685554	\$281 and select\$3 and review and data file	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 14:04
S283	18	\$278 and select\$3 and review and data adj file	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 14:04
S284	17	\$283 and parameters	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 14:04
S285	2	\$277 and \$278 and \$282 and \$284	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 14:04
S286	0	\$285 and @ad<"20030712"	USPAT	OR	ON	2009/06/29 14:04
S288	129	\$231 and(wafer\$1 or semicondudor\$l or chip\$l or subtrat\$1)	USPAT	OR	ON	2009/06/29 14:06
S289	4	\$288 and user adj select\$3 and review and(storage or stored or memory or data adj file)	USPAT	OR	ON	2009/06/29 14:06
S290	0	\$289 and select\$3 adj(wafer\$1 or semicondudor\$l or chip\$l or substrat\$1)and(capturing or pictures or ccd or camera)and align\$4 and(illumination or source or light or optimal adj intensity or brightness or contrast)	USPAT	OR	ON	2009/06/29 14:07
S291	0	\$289 and automatic adj defect and recognition and(detect\$3 or determining)and(defect or flaw or fault)and(assign\$3 or test\$3 or evaluat\$3 or accept\$3)	USPAT	OR	ON	2009/06/29 14:08
S292	3	\$289 and(@ad<"20030712" or @rlad<"20030712" or @prad<"20030712" or @prad<"20030712" or @prad<"20030712" or	USPAT	OR	ON	2009/06/29 14:09
S293	0	\$292 and select\$3 adj(wafer\$1 or semicondudor\$I or chip\$I or substrat\$1)and(capturing or pictures or ccd or camera)and align\$4 and(illumination or source or light or optimal adj intensity or brightness or contrast)	USPAT	OR	ON	2009/06/29 14:23
S294	1	\$288 and automatic adj defect and recognition and(detect\$3 or determining)and(defect or flaw or fault)and(assign\$3 or test\$3 or evaluat\$3 or accept\$3)	USPAT	OR	ON	2009/06/29 14:26
S295	0	\$294 and select\$3 adj(wafer\$1 or semicondudor\$l or chip\$l or substrat\$1)and(capturing or pictures or ccd or camera)and align\$4 and(illumination or source or light or optimal adj intensity or brightness or contrast)	USPAT	OR	ON	2009/06/29 14:26
S296	0	\$294 and user adj select\$3 and review and(storage or stored or memory or data adj file)	USPAT	OR	ON	2009/06/29 14:28

S304	1	((wafer\$1 or semicondudor\$1 or chip\$1 or subtrat\$1) and user adj select\$3 and review and data adj file and input and user and page and learning adj mode).clm.	US-PGPUB	OR	ON	2009/06/29 14:51
S306	1	\$294 and automatic adj defect and recognition and(detect\$3 or determining)and(defect or flaw or fault)and(assign\$3 or test\$3 or evaluat\$3 or accept\$3)	USPAT	OR	ON	2009/06/29 14:55
S307	0	\$306 and select\$3 adj(wafer\$1 or semicondudor\$1 or chip\$1 or substrat\$1)and(capturing or pictures or ccd or camera)and(detect\$3 or determining)and(defect or flaw or fault)and (assign\$3 or test\$3 or evaluat\$3)and align\$4 and(illumination or source or light or optimal adj intensity or light adj intensity or brightness or contrast)	US-PGPUB; USPAT; EPO; JPO; DERWENT; BM_TDB	OR	ON	2009/06/29 14:59
S308	0	\$306 and select\$3 adj(wafer\$1 or semicondudor\$1 or chip\$1 or substrat\$1)and(capturing or pictures or ccd or camera)and(detect\$3 or determining)and(defect or flaw or fault)and (assign\$3 or test\$3 or evaluat\$3)and align\$4 and(illumination or source or light or optimal adj intensity or light adj intensity or brightness or contrast)	USPAT	OR	ON	2009/06/29 14:59
S309	0	accept\$3 adj select\$3 adj(wafer\$1 or semicondudor\$1 or chip\$1 or substrat\$1)and(capturing or pictures or ccd or camera)and(detect\$3 or determining)and(defect or flaw or fault)and (assign\$3 or test\$3 or evaluat\$3)and align\$4 and(illumination or source or light or optimal adj intensity or light adj intensity or brightness or contrast)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 15:14
S310	0	accept\$3 adj select\$3 adj(wafer\$1 or semicondudor\$1 or chip\$1 or substrat\$1)and(capturing or pictures or ccd or camera)and(detect\$3 or determining)and(defect or flaw or fault)and (assign\$3 or test\$3 or evaluat\$3)and(illumination or source or light or optimal adj intensity or light adj intensity or brightness or contrast)	US PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 15:15
S311	0	accept\$3 adj select\$3 adj(wafer\$1 or semicondudor\$1 or chip\$1 or substrat\$1)and(capturing or pictures or ccd or camera)and(detect\$3 or determining)and(defect or flaw or fault)and (assign\$3 or test\$3 or evaluat\$3)and(illumination or source or light or optimal adj intensity or light adj intensity or brightness or contrast)and threshold\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/29 15:17

7/2/09 12:06:03 PM

 $\textbf{C:} \ \, \textbf{Documents and Settings} \ \, \textbf{SChawan} \ \, \textbf{My Documents} \ \, \textbf{EAST} \\ \ \, \textbf{Workspaces} \ \, \textbf{4454.wsp}$